

General Purpose Transistors

PNP Silicon

We declare that the material of product compliance with RoHS requirements.

ORDERING INFORMATION

Device	Marking	Shipping
LBCW68GLT1G	DG	3000/Tape&Reel
LBCW68GLT3G	DG	10000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	- 45	Vdc
Collector–Base Voltage	V_{CBO}	- 60	Vdc
Emitter–Base Voltage	V_{EBO}	- 5.0	Vdc
Collector Current — Continuous	I_C	- 800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR- 5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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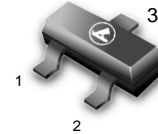
OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = -10 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	- 45	—	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = -10 \mu\text{Adc}, V_{EB} = 0$)	$V_{(BR)CES}$	- 60	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	- 5.0	—	—	Vdc
Collector Cutoff Current ($V_{CE} = -45 \text{ Vdc}, I_E = 0$)	I_{CES}	—	—	- 20	nAdc
($V_{CE} = -45 \text{ Vdc}, I_B = 0, T_A = 150^\circ\text{C}$)		—	—	- 10	μAdc
Emitter Cutoff Current ($V_{EB} = - 4.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	—	- 20	nAdc

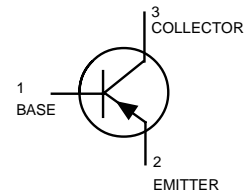
1. FR- 5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

LBCW68GLT1G



CASE 318-08, STYLE 6
SOT-23 (TO-236AB)



LBCW68GLT1G
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
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DC CHARACTERISTICS

DC Current Gain ($I_C = -10\text{ mA dc}$, $V_{CE} = -1.0\text{ V dc}$)	h_{FE}	120	—	400	—
($I_C = -100\text{ mA dc}$, $V_{CE} = -1.0\text{ V dc}$)		160	—	—	
($I_C = -300\text{ mA dc}$, $V_{CE} = -1.0\text{ V dc}$)		60	—	—	
Collector-Emitter Saturation Voltage ($I_C = -300\text{ mA dc}$, $I_B = -30\text{ mA dc}$)	$V_{CE(sat)}$	—	—	-1.5	Vdc
Base-Emitter Saturation Voltage ($I_C = -500\text{ mA dc}$, $I_B = -50\text{ mA dc}$)	$V_{BE(sat)}$	—	—	-2.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

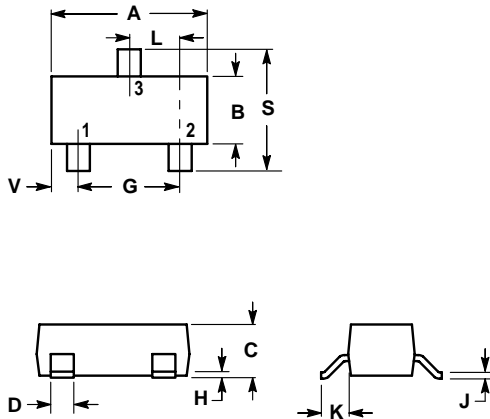
Current-Gain — Bandwidth Product ($I_C = -20\text{ mA dc}$, $V_{CE} = -10\text{ V dc}$, $f = 100\text{ MHz}$)	f_T	100	—	—	MHz
Output Capacitance ($V_{CB} = -10\text{ V dc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	—	18	pF
Input Capacitance ($V_{EB} = -0.5\text{ V dc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	—	—	105	pF
Noise Figure ($V_{CE} = -5.0\text{ V dc}$, $I_C = -0.2\text{ mA dc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF	—	—	10	dB

LBCW68GLT1G

SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

